

Inverter for motor control

600V IGBT Intelligent Power Module (IPM)

BM64375S-VA

General Description

BM64375S-VA is an Intelligent Power Module composed of gate drivers, bootstrap diodes, IGBTs, fly wheel diodes.

Features

- 3phase DC/AC Inverter
- 600V/20A
- Low Side IGBT Open Emitter
- Built -in Bootstrap Diode
- High Side IGBT Gate Driver(HVIC):
 SOI (Silicon On Insulator) Process,
 Drive Circuit, High Voltage Level Shifting,
 Current Limit for Bootstrap Diode,
 Control Supply Under-Voltage Locked Out (UVLO)
- Low Side IGBT Gate Driver(LVIC):
 Drive Circuit, Short Circuit Current Protection (SCP),
 Control Supply Under Voltage Locked Out (UVLO),

Thermal Shutdown (TSD),
Temperature Output by Analog Signal (VOT)

- Fault Signal(LVIC)
 Corresponding to SCP (Low Side IGBT), TSD, UVLO
- Input Interface 3.3V, 5V Line
- UL Recognized: UL1557 File E468261

Application

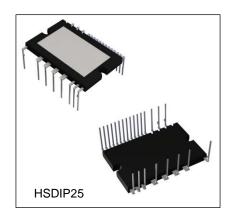
- AC100 to 240Vrms(DC Voltage: Less Than 400V)
 Class Motor Control
- Compressor Motor Control for Air Conditioner, Washing Machine, Refrigerator

Typical Application Circuit

Key Specifications

■ IGBT Collector-Emitter Voltage V_{CESAT}: 1.7V(Typ)
 ■ FWD Forward Voltage V_F: 1.65V(Typ)
 ■ FWD Reverse Recovery Time t_{rr}: 100ns(Typ)
 ■ Module Case Temperature T_C: -25 to +115°C
 ■ Junction Temperature T_{jmax}: 150°C

Package HSDIP25 W(Typ) x D(Typ) x H(Typ) 38.0mm x 24.0mm x 3.5mm



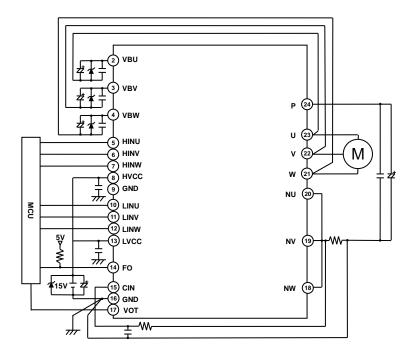


Figure 1. Example of Application Circuit

Pin Configuration

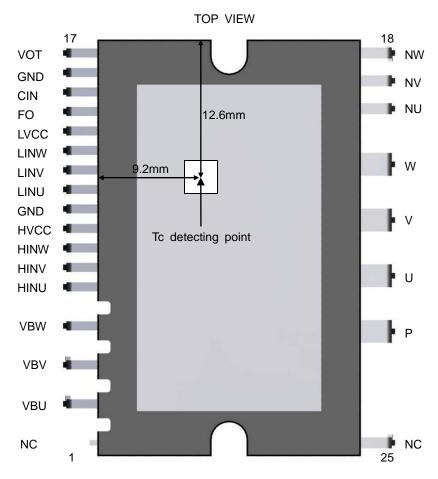


Figure 2. Pin Configuration and Tc Detecting Point

Pin Description

esci iptioi	•				
Pin No.	Pin Name	Function	Pin No.	Pin Name	Function
1	NC	No connection(GND potential)	14	FO	Alarm output
2	VBU	U phase floating control supply	15	CIN	Detecting of short circuit current trip voltage
3	VBV	V phase floating control supply	16	GND	Ground (Note 1)
4	VBW	W phase floating control supply	17	VOT	Temperature output
5	HINU	U phase high side IGBT control	18	NW	W phase low side IGBT emitter
6	HINV	V phase high side IGBT control	19	NV	V phase low side IGBT emitter
7	HINW	W phase high side IGBT control	20	NU	U phase low side IGBT emitter
8	HVCC	Control supply for HVIC	21	W	W phase output
9	GND	Ground (Note 1)	22	V	V phase output
10	LINU	U phase low side IGBT control	23	U	U phase output
11	LINV	V phase low side IGBT control	24	Р	Inverter supply
12	LINW	W phase low side IGBT control	25	NC	No connection (Note 2)
13	LVCC	Control supply for LVIC		•	

⁽Note 1) Two GND pins (9 & 16pin) are connected inside IPM, please connect one pin (16pin is recommended) to the 15V power supply GND outside and leave the other open.

(Note 2) NC pin (25pin) is not electrically connected to any other potential inside.

Block Diagram

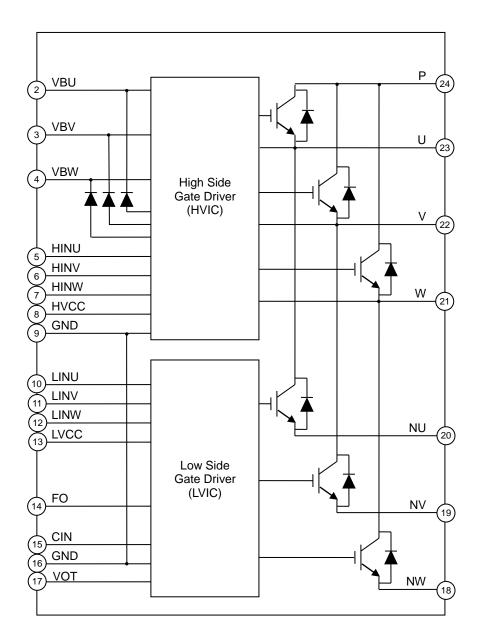


Figure 3. Block Diagram

Description of Block

1) High Side IGBT Drive (HVIC, Bootstrap Diode)

High voltage level shifting circuit drives high side IGBT.

Built-in bootstrap diode and current limit function for bootstrap diode enable HVIC to drive high side IGBT without external component (bootstrap diode, resistor). There is under-voltage-locked-out (UVLO) function for floating control power supply.

2) Low Side IGBT Drive (LVIC)

LVIC drives low side IGBT.

There is short circuit current protection (SCP), under-voltage locked out (UVLO) for control power supply LVCC, thermal shutdown (TSD) function. Alarm signal (FO) will output when these protection circuits work.

LVIC detects temperature of itself, transform temperature into analog voltage, and output voltage to VOT pin.

Absolute Maximum Ratings (Unless otherwise specified, Tj=25°C) Inverter Part

Item	Item		Ratings	Unit	Conditions		
Supply Voltage		V_P	450	V	Applied between P-NU,NV,NW		
Supply Voltage(Su	Supply Voltage(Surge)		500	V	Applied between P-NU,NV,NW		
Collector-Emitter \	Collector-Emitter Voltage		600	V			
Collector Current	DC	lc	±20 (Note 1)	Α	T _C =25°C		
Collector Current	PEAK	ICP	±40 (Note 1)	Α	T _C =25°C, less than 1ms		
Collector Power Dissipation		Pc	41	W	T _C =25°C, per 1 chip		
Junction Temperature		T _{jmax}	150	°C			

(Note 1) Do not, however exceed Pc, ASO.

Control part

Item	Item Symbol Ratings		Unit	Conditions
Control Power Supply	Vcc	20	V	Applied between HVCC-GND, LVCC-GND
Floating Control Power Supply	V_{BS}	20	V	Applied between VBU-U, VBV-V, VBW-W
Control Input Voltage	V _{IN}	-0.5 to V _{CC} +0.5	V	Applied between HINX, LINX-GND (X=U,V,W)
Fault Output Supply Voltage	V_{FO}	-0.5 to V _{CC} +0.5	V	Applied between FO-GND
Fault Output Current	I _{FO}	1	mA	Sink current at FO pin
Current Sensing Input Voltage	Vcin	-0.5 to +7.0	V	Applied between CIN-GND
Temperature Output Voltage	Vот	-0.5 to +7.0	V	Applied between VOT-GND

Bootstrap diode part

Item	Symbol	Ratings	Unit	Conditions
Reverse Voltage	V_{RB}	600	V	
Junction Temperature	T_{jmaxD}	150	°C	

Total system

Item	Symbol	Ratings	Unit	Conditions
Self Protection Supply Voltage (SCP Capability)	V _P (PROT)	400	V	V _{CC} =13.5 to 16.5V, Inverter part T _j =125°C, non-repetitive, less than 2µs
Module Case Temperature	odule Case Temperature Tc -25 to +115		°C	Measurement point of T _C is provided in Figure 2
Storage Temperature	T _{stg}	-40 to +125	°C	
Isolation Voltage	V _{iso}	1500	V _{rms}	Sinusoidal, 60Hz, AC 1min, between connected all pins and heat sink plate

Thermal resistance

			Limit			Conditions
Item	Symbol	Min	Тур	Max	Unit	
Junction to Case Thermal	R _{th(j-c)_IGBT}	-	-	3.0	°C /W	Inverter IGBT(1/6 module)
Resistance (Note 2)	R _{th(j-c)_FWD}	-	-	3.9	°C /W	Inverter FWD(1/6 module)

⁽Note 2) Grease with good conductivity and high reliability should be applied evenly with +100 to +200µm on the contacting surface of IPM and heat sink. Use a torque wrench to fasten up to the specified torque rating. The contacting thermal resistance between IPM case and heat sink is determined by the thickness and the thermal conductivity of the applied grease.

Caution: Operating the IPM over the absolute maximum ratings may damage the IPM. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IPM is operated over the absolute maximum ratings.

Recommended Operating Conditions

lta	Comple al		Limit		Lloit	Conditions
Item	Symbol	Min	Тур	Max	Unit	
Supply Voltage	VP	0	300	400	V	Applied between P-NU,NV,NW
Control Power Supply	Vcc	13.5	15.0	16.5	V	Applied between HVCC-GND, LVCC-GND
Floating Control Power Supply	V _{BS}	13.0	15.0	18.5	V	Applied between VBU-U, VBV-V, VBW-W
Control Power Supply Variation	⊿Vcc ⊿Vвs	-1	-	+1	V/µs	
Control Input Voltage	Vin	0	-	5.5	V	
Current Sensing Input Voltage	V _{CIN}	0	-	5.5	V	
Blanking Time for Preventing Arm-short	t _{dead}	1.0	-	-	μs	For each input signal
PWM Input Frequency	f _{PWM}	-	-	20	kHz	T _C ≤ 100°C, T _j ≤ 125°C
High Side IGBT	PWonh	0.8	-	-	μs	
Minimum Input Pulse Width ^(Note1)	PWoffh	0.8	-	-	μs	
Low Side IGBT	PWonL	0.8	-	-	μs	
Minimum Input Pulse Width ^(Note1)	PW _{OFFL}	0.8	-	-	μs	
Voltage Variation Between GND- NU, NV, NW	V _N	-5	-	+5	V	Between GND-NU, NV, NW (Including surge voltage)
Junction Temperature	Tj	-25	-	+125	°C	

(Note 1) IPM might not respond if the input signal pulse width is less than PW_{ON}, PW_{OFF}.

Electrical Characteristics (Unless otherwise specified, Tj=25°C, Vcc=VBS=15V, VP=300V) Inverter Part

ltom	Cumbal		Limit		Unit	Conditions	
Item	Symbol	Min	Тур	Max	Unit	Conditions	
Collector Emitter Seturation Voltage	\/	-	1.70	2.15	V	Ic=20A	
Collector-Emitter Saturation Voltage	VCESAT	-	0.90	1.20	V	Ic=2A	
Collector-Emitter Cut-off Current	Ices	-	-	100	μA	Vce=Vces	
FWD Forward Voltage	VF	-	1.65	2.15	V	I _F =20A	
FWD Reverse Recovery Time	t _{rr}	-	100	-	ns	Inductive Load, I _C =20A	
High Side IGBT Turn on Delay Time	tonH	0.75	1.25	1.85	μs	Inductive Load, I _C =20A	
High Side IGBT Turn on Switching Time	t _{c(on)H}	-	0.35	-	μs	Inductive Load, I _C =20A	
High Side IGBT Turn off Delay Time	t _{offH}	-	1.10	1.70	μs	Inductive Load, I _C =20A	
High Side IGBT Turn off Switching Time	t _{c(off)} H	-	0.15	-	μs	Inductive Load, I _C =20A	
Low Side IGBT Turn on Delay Time	tonL	0.75	1.25	1.85	μs	Inductive Load, I _C =20A	
Low Side IGBT Turn on Switching Time	t _{c(on)L}	-	0.40	-	μs	Inductive Load, I _C =20A	
Low Side IGBT Turn off Delay Time	t _{offL}	-	1.40	2.00	μs	Inductive Load, I _C =20A	
Low Side IGBT Turn off Switching Time	t _{c(off)L}	-	0.15	-	μs	Inductive Load, Ic=20A	

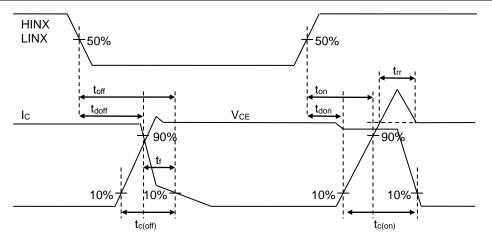


Figure 4. Switching Time Definition

Control part

Item	miles part			Limit			
Whole VCC Circuit Current 1 ICc1 - 1.20 2.40 mA V _{IN} =0V VCC Circuit Current 2 Icc2 - 1.40 2.80 mA V _{IN} =5V VBS Circuit Current 1 Iss1 - 0.06 0.15 mA V _{IN} =6V VBS Circuit Current 2 Iss2 - 0.06 0.15 mA V _{IN} =6V Control Input(HINU,HINV,HINV,LINV,LINV) Input 0.7 1.0 1.5 mA V _{IN} =5V Control Input Current Ink1 -10 - - μA V _{IN} =5V L Level Input Threshold Voltage V _{IN} 1 - - - μA V _{IN} =0V H Level Input Threshold Voltage V _{IN} 1 - - - V Input Hysteresis Voltage V _{IN} 1 - - - V HINU-GND Resistance (Note 1) R _{ININ} 1 35 50 68 kΩ HVCC=0V, I _{ININ} =2μA HINW-GND Resistance (Note 1) R _{ININ} 1 70 100 136	Item	Symbol	Min		Max	Unit	Conditions
VCC Circuit Current 2 Icc2 - 1.40 2.80 mA V _{IN=5} V VBS Circuit Current 1 Ias1 - 0.06 0.15 mA V _{IN=5} V VBS Circuit Current 2 Ias2 - 0.06 0.15 mA V _{IN=5} V Control Input(HINU,HINV,LINU,LINV,LINW) Level Input Current IINH 0.7 1.0 1.5 mA V _{IN=5} V Level Input Current IINH -10 - - μA V _{IN=5} V Level Input Threshold Voltage V _{INH} - - 2.6 V Level Input Threshold Voltage V _{INH} - - 2.6 V Level Input Threshold Voltage V _{INH} 0.8 - - V Input Hysteresis Voltage V _{INYS} - 0.25 - V Input Hysteresis Voltage V _{INYS} - 0.25 - V HINU-GND Resistance (Note1) R _{HINU} 70 100 136 KΩ HVCC=0V, I _{HINU} =2μA HINU-GND Resistance (Note1) R _{HINV} 70 100 136 KΩ HVCC=0V, I _{HINV} =2μA HINW-GND Resistance (Note1) R _{HINV} 70 100 136 KΩ HVCC=0V, I _{HINV} =2μA HINW-GND Resistance (Note1) V _{SC} 0.455 0.480 0.505 V Under Voltage V _{CCUVR} 11 12 13 V VCC Trip Voltage V _{CCUVR} 11 12 13 V VCC Release Voltage V _{CCUVR} 11 12 13 V VBS Release Voltage V _{CCUVR} 10.5 11.5 12.5 V VBS Release Voltage V _{SSUV} 10 11 12 V VBS Release Voltage V _{SSUV} 10.5 11.5 12.5 V Thermal Shutdown(TSD) Trip Temperature T _{SDT} 115 130 - °C Monitor LVIC temperature Hysteresis Temperature T _{SDHYS} - 20 - °C Monitor LVIC temperature Temperature Output(VOT) VOT Voltage V _{FO} 2.72 2.77 2.82 V LVIC temperature 25°C Fault Output (Notage V _{FO} - - 0.95 V I _{FO} =1mA Leak Current I _{FOUL} 45 -	Whole			, , , , , , , , , , , , , , , , , , ,			
VBS Circuit Current 1	VCC Circuit Current 1	Icc1	-	1.20	2.40	mA	V _{IN} =0V
VBS Circuit Current 2	VCC Circuit Current 2	I _{CC2}	-	1.40	2.80	mA	V _{IN} =5V
Control Input(HINU,HINV,HINW,LINU,LINV)	VBS Circuit Current 1	I _{BS1}	-	0.06	0.15	mA	V _{IN} =0V
H Level Input Current	VBS Circuit Current 2	I _{BS2}	-	0.06	0.15	mA	V _{IN} =5V
Level Input Current	Control Input(HINU,HINV,HINW	LINU,LINV	,LINW)	<u>I</u>			1
H Level Input Threshold Voltage	H Level Input Current	linh	0.7	1.0	1.5	mA	V _{IN} =5V
Level Input Threshold Voltage	L Level Input Current	I _{INL}	-10	-	-	μΑ	V _{IN} =0V
Input Hysteresis Voltage	H Level Input Threshold Voltage	Vinh	-	-	2.6	V	
HINU-GND Resistance (Note 1) RHINU 35 50 68 KΩ HVCC=0V, IHINU=2μA HINV-GND Resistance (Note 1) RHINV 70 100 136 KΩ HVCC=0V, IHINV=2μA HINW-GND Resistance (Note 1) RHINW 70 100 136 KΩ HVCC=0V, IHINV=2μA HINW-GND Resistance (Note 1) RHINW 70 100 136 KΩ HVCC=0V, IHINV=2μA Short Circuit Current Protection(SCP) CIN Input Bias Current IciN -2 -	L Level Input Threshold Voltage	V _{INL}	0.8	-	-	V	
HINV-GND Resistance (Note 1) RHINV 70 100 136 KΩ HVCC=0V, IHINV=2μA	Input Hysteresis Voltage	V _H ys	-	0.25	-	V	
HINW-GND Resistance (Note 1) R _{HINW} 70 100 136 kΩ HVCC=0V, I _{HINW} =2μA	HINU-GND Resistance (Note 1)	R _{HINU}	35	50	68	kΩ	HVCC=0V, I _{HINU} =2µA
Short Circuit Current Protection(SCP) CIN Input Bias Current	HINV-GND Resistance (Note 1)	R _{HINV}	70	100	136	kΩ	HVCC=0V, I _{HINV} =2µA
CIN Input Bias Current Icin -2 - - μA CIN=0V	HINW-GND Resistance (Note 1)	R _{HINW}	70	100	136	kΩ	HVCC=0V, I _{HINW} =2µA
Trip Voltage	Short Circuit Current Protectio	n(SCP)					
Under Voltage Locked Out(UVLO)	CIN Input Bias Current	I _{CIN}	-2	-	-	μA	CIN=0V
VCC Trip Voltage V _{CCUVT} 10.5 11.5 12.5 V VCC Release Voltage V _{CCUVR} 11 12 13 V VBS Trip Voltage V _{BSUVT} 10 11 12 V VBS Release Voltage V _{BSUVR} 10.5 11.5 12.5 V Thermal Shutdown(TSD) Trip Temperature T _{SDT} 115 130 - °C Monitor LVIC temperature Hysteresis Temperature T _{SDHYS} - 20 - °C Monitor LVIC temperature Temperature Output(VOT) VOT 2.72 2.77 2.82 V LVIC temperature = 90°C VOT Voltage Vot 0.93 1.13 1.33 V LVIC temperature = 25°C Fault Output(FO) Output low Voltage V _{FO} - - 0.95 V I _{FO} =1mA Leak Current I _{FO} LEAK - - 10 µA V _{FO} =5V Output Pulse Width (Note 2) 1 -<	Trip Voltage	Vsc	0.455	0.480	0.505	V	
VCC Release Voltage VCCUVR 11 12 13 V VBS Trip Voltage VBSUVT 10 11 12 V VBS Release Voltage VBSUVR 10.5 11.5 12.5 V Thermal Shutdown(TSD) Trip Temperature TSDT 115 130 - °C Monitor LVIC temperature Hysteresis Temperature TSDHYS - 20 - °C Monitor LVIC temperature Temperature Output(VOT) VOT 2.72 2.77 2.82 V LVIC temperature = 90°C VOT Voltage VoT 0.93 1.13 1.33 V LVIC temperature = 25°C Fault Output(FO) Output low Voltage VFO - - 0.95 V IFO=1mA Leak Current IFOSE 45 - - µs During SCP Operation Output Pulse Width (Note 2) TFOUV 90 - - µs During VCC UVLO Operation	Under Voltage Locked Out(UVL	.O)		1	i.		
VBS Trip Voltage V _{BSUVT} 10 11 12 V VBS Release Voltage V _{BSUVR} 10.5 11.5 12.5 V Thermal Shutdown(TSD) Trip Temperature T _{SDT} 115 130 - °C Monitor LVIC temperature Hysteresis Temperature T _{SDHYS} - 20 - °C Monitor LVIC temperature Temperature Output(VOT) VOT Voltage Vot 2.72 2.77 2.82 V LVIC temperature = 90°C VOT Voltage Vot 0.93 1.13 1.33 V LVIC temperature = 25°C Fault Output(FO) Output low Voltage VFO - - 0.95 V IFO=1mA Leak Current IFOLEAK - - 10 μA VFO=5V Output Pulse Width (Note 2) TFOUV 90 - - μs During VCC UVLO Operation	VCC Trip Voltage	Vccuvt	10.5	11.5	12.5	V	
VBS Release Voltage VBSUVR 10.5 11.5 12.5 V Thermal Shutdown(TSD) Trip Temperature TSDT 115 130 - °C Monitor LVIC temperature Hysteresis Temperature TSDHYS - 20 - °C Monitor LVIC temperature Temperature Output(VOT) VOT Voltage Vot UVIC temperature = 90°C VOT Voltage Vot UVIC temperature = 25°C Fault Output(FO) Output low Voltage VFO O.95 V IFO=1mA Leak Current IFOLEAK 10 µA VFO=5V Leak Current IFOSC 45 µs During SCP Operation Output Pulse Width (Note 2) IFOUV 90 µs During VCC UVLO Operation	VCC Release Voltage	Vccuvr	11	12	13	V	
Thermal Shutdown(TSD)	VBS Trip Voltage	V _{BSUVT}	10	11	12	V	
Trip Temperature T_{SDT} 115 130 - °C Monitor LVIC temperature Hysteresis Temperature T_{SDHYS} - 20 - °C Monitor LVIC temperature T_{SDHYS} - 2.82 V LVIC temperature = 90°C T_{SDHYS} - 2.82 V LVIC temperature = 25°C T_{SDHYS} - 2.82 V LVIC temperature = 90°C T_{SDHYS}	VBS Release Voltage	V _{BSUVR}	10.5	11.5	12.5	V	
Hysteresis Temperature T_{SDHYS} - 20 - °C Monitor LVIC temperature T_{SDHYS} - 20 - °C Monitor LVIC temperature T_{SDHYS} - 20 - °C Monitor LVIC temperature T_{SDHYS} - 2.72 2.77 2.82 V LVIC temperature = 90°C 0.93 1.13 1.33 V LVIC temperature = 25°C T_{SDHYS} - 2.82 V LVIC temp	Thermal Shutdown(TSD)						
Vot Vot Voltage Vot Vot 2.72 2.77 2.82 V LVIC temperature = 90°C	Trip Temperature	T _{SDT}	115	130	-	°C	Monitor LVIC temperature
$VoT\ Voltage \qquad VoT \qquad 2.72 \qquad 2.77 \qquad 2.82 \qquad V \qquad LVIC\ temperature = 90°C \\ \hline 0.93 \qquad 1.13 \qquad 1.33 \qquad V \qquad LVIC\ temperature = 25°C \\ \hline \textit{Fault Output(FO)} \\ \hline Output low\ Voltage \qquad VFO \qquad - \qquad - \qquad 0.95 \qquad V \qquad IFO=1mA \\ Leak\ Current \qquad IFOLEAK \qquad - \qquad - \qquad 10 \qquad \mu A \qquad VFO=5V \\ \hline \textit{LFOSC} \qquad 45 \qquad - \qquad - \qquad \mu s \qquad During\ SCP\ Operation \\ \hline Output\ Pulse\ Width\ ^{(Note\ 2)} \qquad 1FOUV \qquad 90 \qquad - \qquad - \qquad \mu s \qquad During\ VCC\ UVLO\ Operation \\ \hline \end{tabular}$	Hysteresis Temperature	T _{SDHYS}	-	20	-	°C	Monitor LVIC temperature
VoT 0.93 1.13 1.33 V LVIC temperature = 25°C Fault Output(FO) Output low Voltage VFO - - 0.95 V IFO=1mA Leak Current IFOLEAK - - 10 μA VFO=5V Leak Current tFOSC 45 - - μs During SCP Operation Output Pulse Width (Note 2) tFOUV 90 - - μs During VCC UVLO Operation	Temperature Output(VOT)						
0.93	VOT Voltage	\/	2.72	2.77	2.82	V	LVIC temperature = 90°C
Output low Voltage VFO - - 0.95 VIF0=1mA Leak Current IFOLEAK - - 10 μA VF0=5V tFOSC 45 - - μs During SCP Operation Output Pulse Width (Note 2) tFOUV 90 - - μs During VCC UVLO Operation	voi vollage	VOT	0.93	1.13	1.33	V	LVIC temperature = 25°C
Leak Current IFOLEAK - - 10 μΑ VFO=5V tFOSC 45 - - μs During SCP Operation Output Pulse Width (Note 2) tFOUV 90 - - μs During VCC UVLO Operation	Fault Output(FO)	<u> </u>					
t _{FOSC} 45 - μs During SCP Operation Output Pulse Width (Note 2) t _{FOUV} 90 - μs During VCC UVLO Operation	Output low Voltage	VFO	-		0.95	V	I _{FO} =1mA
Output Pulse Width (Note 2) t _{FOUV} 90 µs During VCC UVLO Operation	Leak Current	IFOLEAK	-	-	10	μA	V _{FO} =5V
		trosc	45	-	-	μs	During SCP Operation
t _{FOTSD} 180 μs During TSD Operation	Output Pulse Width (Note 2)	t _{FOUV}	90	-	-	μs	During VCC UVLO Operation
		trotsd	180	-	-	μs	During TSD Operation

Bootstrap Diode Part

Item	Symbol	Symbol Limit			Unit	Conditions
item	Symbol	Min	Тур	Max	Unit	Conditions
Farmer Mallana	V _{FB1}	0.3	0.6	0.9	V	I _{FB} =1mA Voltage drop between HVCC-VBX (X=U,V,W)
Forward Voltage	V _{FB2}	1.1	2.0	2.9	V	Voltage drop between HVCC-VBX (X=U,V,W)
Reverse Current	I_{RB}	-	-	10	μA	V _{RB} =600V
Reverse Recovery Time	t _{rrB}	-	80	-	ns	I _{FB} =0.1A

⁽Note 1) Resistance value when current from the control input pin is flowing through the internal resistor to GND.

(Note 2) FO pulse width for each protection mode is different. FO will continue to output until recovering from the error condition if the time of error condition exceeds the determined output pulse width depending on the protection mode.

Mechanical Characteristics And Ratings

Item	Limit			Unit	Following Standard	Conditions
nem	Min	Тур	Max	Unit	Following Standard	Conditions
Mounting Torque	0.59	0.69	0.78	N∙m	-	Mounting Screw M3 (Note 1) Recommended 0.69N·m (Note 2)
Pin Pulling Strength	10	-	-	s	EIAJ-ED-4701/400	Load Control Pin:4.9N Power Pin:9.8N
Pin Bending Strength	2	-	-	times	EIAJ-ED-4701/400	Load Control Pin: 2.45N Power Pin:4.9N 90deg. Bend
Weight	-	10	-	g	-	
Heat Sink Flatness	0	-	+200	μm	-	Measurement point is provided in Figure 6-1.

(Note 1) Plain washers of 8mm outside diameter (ISO 7089 to 7094) are recommended.

(Note 2) When installing a module to a heat sink, excessive uneven fastening force might apply stress to inside chips or ceramic of heat sink plate, which will break or crack or degrade a module. An example of recommended fastening sequence is shown in Figure 5. The temporary fastening torque is set to 20 to 30% of the maximum torque rating. Evenly apply thermally-conductive grease with 100µm to 200µm thickness over the contact surface between the module and the heat sink. Also, pay attention not to have any dirt left on the contact surface between the module and the heat sink. It is recommended to install a module directly to a heat sink after applying grease. When installing a module to a heat sink, inserting a heat radiation sheet between a module and a heat sink might apply stress depending on thickness and elastic modulus of the sheet to inside chips or ceramic of heat sink plate, which will break or crack or degrade a module. When using a heat radiation sheet, it is needed to prevent IPM from bending into + side of Figure 6-2.

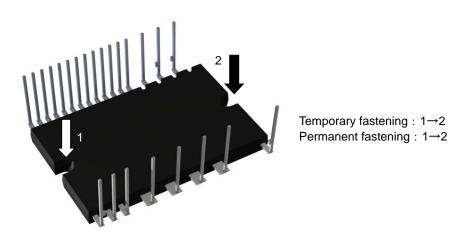


Figure 5. Example of Recommended Fastening Sequence

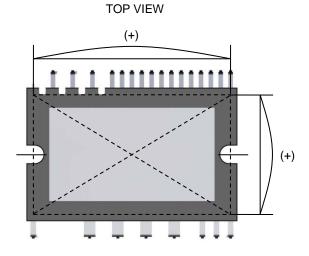


Figure 6-1. Measurement Point of Heat Sink Flatness

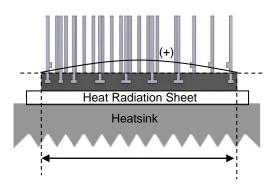


Figure 6-2. Flatness after Installing to a Heat Sink (When Using a Heat Radiation Sheet)

Typical Performance Curve

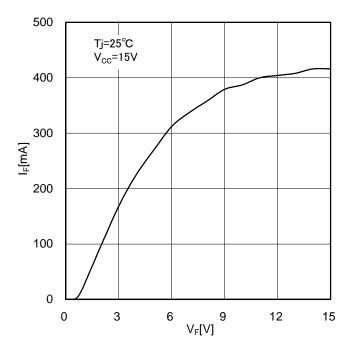


Figure 7. I_F vs V_F

Characteristic of Bootstrap Diode I_F-V_F Curve
Between HVCC-VBX pin (X=U,V,W)

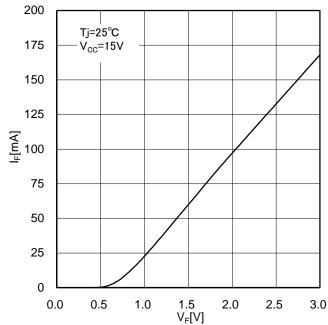


Figure 8. Magnification of Figure 7

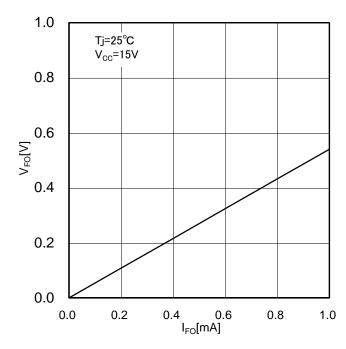
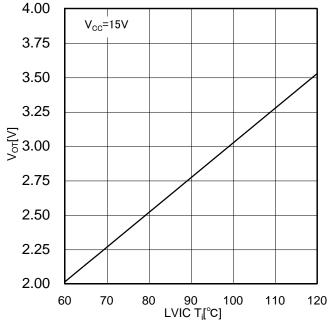


Figure 9. V_{FO} vs I_{FO} (Characteristic of FO pin V_{FO}-I_{FO} Curve)



 $\label{eq:figure 10. Vot vs LVIC T} Figure 10. \ V_{OT} \ vs \ LVIC \ T_{j} \\ (Characteristic of VOT pin V_{OT} - T_{j} \ Curve)$

Timing Chart

- 1) Short Circuit Current Protection (protection with the external shunt resistor and RC filter)
 - a1. Normal operation: IGBT ON and outputs current Ic.
 - a2. Short circuit current detection (SCP trigger)
 - It is recommended to set RC time constant of 1.0µs so that IGBT shuts down within 2.0µs when SCP is triggered.
 - a3. All low side IGBT's gates are shut down (soft turn off).
 - a4. All low side IGBTs turn off.
 - a5. FO outputs for $t_{FO}=45\mu s$ (Min).
 - a6. LIN=L
 - a7. LIN=H, but all IGBTs keep OFF during SCP=H.
 - a8. FO finishes output , but IGBTs don't turn on until inputting the next ON signal(LIN=L→H) IGBT of each phase can return to normal state by inputting ON signal to each phase.
 - a9. Normal operation: IGBT ON and outputs current Ic.

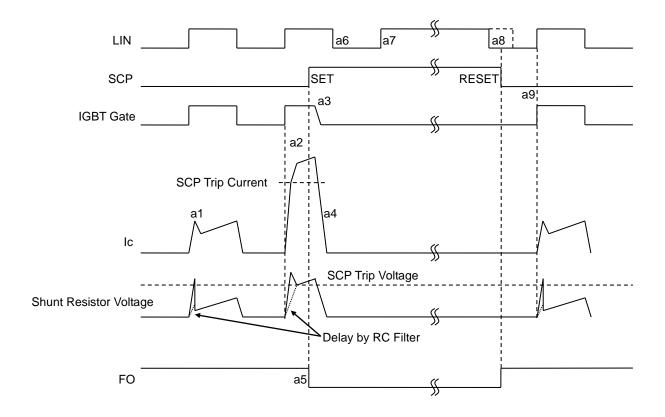


Figure 11. SCP Timing Chart

Notice

SCP works only for low side IGBT only.

Please select the external shunt resistance such that the SCP trip current is less than 1.7 times of the collector current rating $I_c(DC)$.

In case of SCP trip and FO output, please stop controlling IPM quickly to avoid the abnormal state.

- 2) Control Supply (LVCC) Under Voltage Locked Out (UVLO)
 - b1. Control supply(LVCC) voltage exceeds UVLO release level (V_{CCUVR}), but IGBT turns on by the next ON signal (LIN=L→ H).IGBT of each phase can return to normal state by inputting ON signal to each phase.
 - b2. Normal operation: IGBT ON and outputs current Ic.
 - b3. LVCC drops to UVLO trip level (VCCUVT).
 - b4. All low side IGBTs turn off in spite of control input condition.
 - b5. FO outputs for tFo=minimum 90µs, but output is extended while LVCC is below VCCUVR.
 - b6. LVCC reaches V_{CCUVR}.
 - b7. Even if LVCC reaches VCCUVR during LIN=H, IGBTs don't turn on until inputting the next ON signal (LIN=L→H).
 - b8. Normal operation: IGBT ON and outputs current $I_{\text{C.}}$

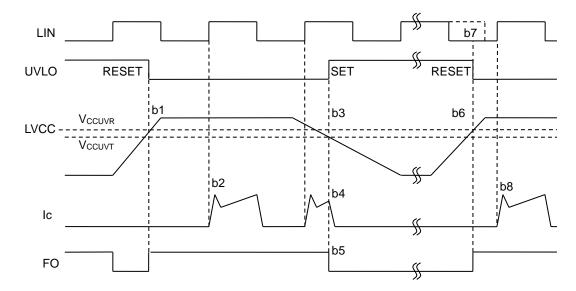


Figure 12. LVCC UVLO Timing Chart

- 3) Control supply (VBS) Under Voltage Locked Out (UVLO)
 - c1. Control supply(VBS) voltage exceeds UVLO release level (V_{BSUVR}), but IGBT turns on by the next ON signal (HIN=L→H).
 - c2. Normal operation: IGBT ON and outputs current Ic.
 - c3. VBS drops to UVLO trip level (VBSUVT).
 - c4. Only IGBT of the corresponding phase turns off in spite of control input signal, there is no FO signal output.
 - c5. VBS reaches V_{BSUVR}.
 - c6. Even if VBS reaches V_{BSUVR} during HIN=H, IGBTs don't turn on until inputting the next ON signal (HIN=L→H).
 - c7. Normal operation: IGBT ON and outputs current Ic.

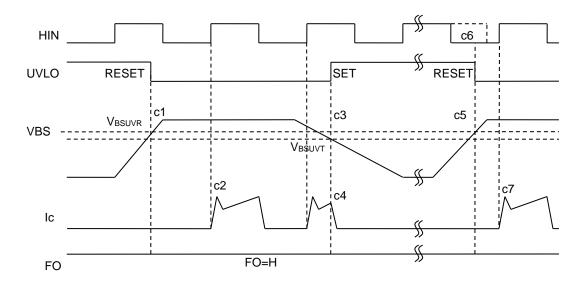


Figure 13. VBS UVLO Timing Chart

- 4) Thermal Shutdown (TSD), monitoring LVIC temperature
 - d1. Normal operation: IGBT ON and outputs current Ic.
 - d2. LVIC temperature (T_i) exceeds thermal shutdown trip level (T_{SDT}).
 - d3. All low side IGBTs turn off in spite of control input condition.
 - d4. FO outputs for tFO=180µs (Min),
 - but output is extended while T_j is above thermal shutdown release level (T_{SDT}-T_{SDHYS}).
 - d5. T_i drops to T_{SDT}-T_{SDHYS}
 - d6. Even if T_j reaches T_{SDT}-T_{SDHYS} during LIN=H, IGBTs don't turn on until inputting the next ON signal (LIN=L→H). IGBT of each phase can return to normal state by inputting ON signal to each phase.
 - d7. Normal operation: IGBT ON and outputs current Ic.

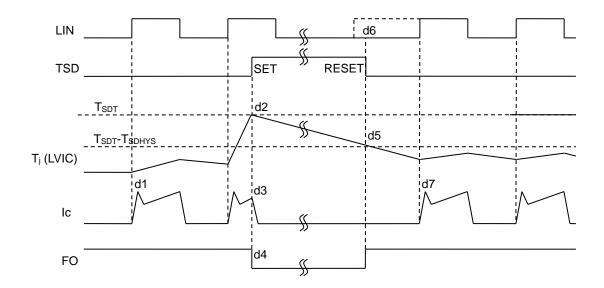


Figure 14. TSD Timing Chart

Notice

- 1) In case of TSD trip and FO output, please stop controlling IPM quickly to avoid the abnormal state.
- 2) If the cooling system is in abnormal state (e.g. heat sink comes off, fixed loosely, or cooling fan stops) when TSD trips, don't reuse IPM. This may cause the junction temperature of power chips to exceed its maximum rating of T_{jmax} (150°C).
- 3) TSD function detects LVIC temperature, so it cannot respond to rapid temperature rise of power chip. Therefore, TSD will not work properly in the case of rapid temperature rise like motor lock or over current.

Application Example (one shunt resistor drive)

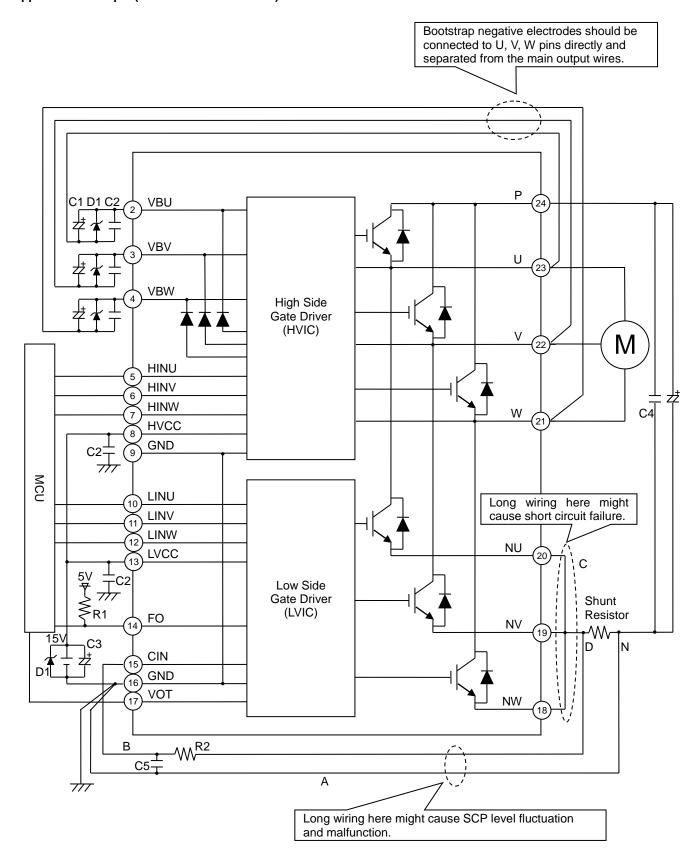


Figure 15. Example of Application Circuit

Selection of Components Externally Connected (Refer to Figure 15)

1) VBU, VBV, VBW pin

- The bypass capacitor(good temperature, frequency characteristic electrolytic type C1: $22\mu\text{F}$ to $100\mu\text{F}$) should be mounted as close as possible to the pin in order to prevent malfunction or destruction due to switching noise and power supply ripple. In addition, for the purpose of reducing of the power supply's impedance in wide frequency bandwidth, ceramic capacitor (good temperature, frequency and DC bias characteristic ceramic type C2: $0.1\mu\text{F}$ to $0.22\mu\text{F}$) should also be mounted.
- · Zenner diode D1(1W) should be mounted between each pair of control supply pins to prevent surge destruction.
- Line ripple voltage should meet dV/dt ≤1V/µs, V_{ripple} ≤ 2V_{p-p.}
- The wiring from U, V, W pin should be as thick and as short as possible. They should be connected directly and separated from the main output wires.

2) HVCC, LVCC pin

- The bypass capacitor(good temperature, frequency characteristic electrolytic type C3) should be mounted as close as possible to the pin in order to prevent malfunction or destruction due to switching noise and power supply ripple. In addition, for the purpose of reducing of the power supply's impedance in wide frequency bandwidth, ceramic capacitor (good temperature, frequency and DC bias characteristic ceramic type C2: 0.1µF to 0.22µF) should also be mounted.
- · Zenner diode D1(1W) should be mounted between each pair of control supply pins to prevent surge destruction.
- Line ripple voltage should meet dV/dt ≤ 1V/µs, V_{ripple} ≤ 2V_{p-p.}

3) P pin

- To prevent surge destruction, the wiring between the smoothing capacitor and P, N pins should be as short as possible.
- Snubber capacitor(C4: 0.1µF to 0.22µF) should be mounted between the P-N pin.

4) Control Input pin (HINU, HINV, HINW, LINU, LINV, LINW)

- The wiring should be as short as possible to prevent malfunction.
- Input drive is active-high type. There is a 3.3kΩ(Min) pull-down resistor in the input circuit of IPM. When using RC coupling circuit, make sure the input signal level meet the input threshold voltage.
- Dead time of input signal should be more than specified value.
- The pull-down resistors in Control Input pins become effective when voltage supplied into LVCC and HVCC pins are in the range of recommended operating condition. Control Input pins have high impedance when power supply to LVCC and HVCC pins are off. When power supply to HVCC pin is off, the pull-down resistance of HINU, HINV, HINW pins is the value written on Page 6.

5) FO pin

• FO output is open drain type. It should be pulled up to control power supply(e.g. 5V, 15V) by a resistor that makes I_{FO} up to 1mA.I_{FO} is estimated roughly by the formula of control power supply voltage divided by pull-up resistance(R1). In the case of pulled up to 5V, R1=10kΩ is recommended.

6) CIN pin

- RC filter(R2, C5) should be mounted as close as possible to the pin in order to prevent malfunction by recovery current or switching noise. It is recommended to select tight tolerance, temp-compensated type for RC filter (R2, C5). The time constant R2C5 (1.0µs is recommended) should be set so that SCP current is shut down within 2µs. Please confirm operation on the actual application since SCP shutdown time changes depending on the PCB wiring pattern.
- The point D at which the wiring to CIN filter is divided should be near the pin of shunt resistor. NU, NV, NW pin should be connected at near NU, NV, NW pin.
- To prevent malfunction, the wiring of B should be as short as possible.

7) VOT pin (Refer to Fugure 16)

- It is recommended to insert $5.1k\Omega$ pull down resistor for getting linear output characteristics at lower temperature than room temperature. When the pull down resistor is inserted between VOT and GND (control GND), the extra current calculated by VOT output voltage divided by pull down resistance flows as LVIC circuit current continuously. In the case of only using VOT for detecting higher temperature than room temperature, it isn't necessary to insert the pull down resistor.
- In the case of using VOT with low voltage controller (e.g. 3.3V MCU), VOT output might exceed control supply voltage 3.3V when temperature rises excessively. If system uses low voltage controller, it is recommended to insert a clamp diode between control supply of the controller and VOT for preventing over voltage.
- In the case of using low voltage controller like 3.3V MCU, if it is necessary to set the trip VOT level to control supply voltage (e.g. 3.3V) or more, there is the method of dividing the VOT output by resistance voltage divider circuit and then inputting to A/D converter on MCU. In that case, sum of the resistances of divider circuit should be as much as 5kΩ.
- When VOT pin is not used, please do not connect VOT pin to any other nodes.
- · Please refer the application note for this product about the usage of VOT output.

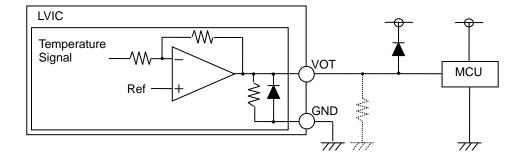


Figure 16. Example of VOT External Circuit

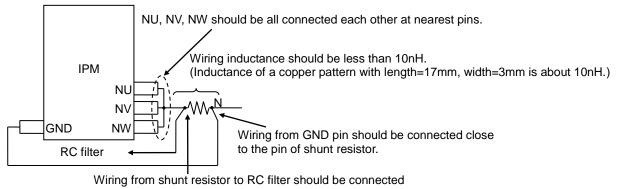
8) GND pin

- Two GND pins (9 & 16 pin) are connected inside IPM. Please connect one pin (16 pin is recommended.) to the 15V power supply GND outside and leave the other open.
- If control GND is connected with power GND by common broad pattern, it may cause malfunction by power GND fluctuation. It is recommended to connect control GND and power GND at only a point N (near the pin of shunt resistor).
- To prevent malfunction, the wiring of A should be as short as possible.

9) NU, NV, NW pin

• When operating with one-shunt resistor, please short the three pins(NU, NV, NW). In addition, to prevent malfunction, the wiring of C should be as short as possible.

10) One-shunt Resistor Drive



near the pin of shunt resistor.

Low inductance shunt resistor like surface mounted (SMD) type is recommended.

Figure 17. Wiring Pattern around the Shunt Resistor when Operating with One-shunt Resistor

11) Three-shunt Resistors Drive

- It is not recommended to input the voltage of each shunt resistor directly to the CIN pin when IPM is operated with three shunt resistor. In that case, it is necessary to use the external protection circuit as below.
- It is necessary to set the time constant $R_u f_f(1.0 \mu s)$ is recommended) of external comparator input so that IGBT stops within $2\mu s$ when short circuit occurs. Please confirm operation on the actual application since SCP shutdown time changes depending on the PCB wiring pattern.
- It is recommended for the threshold voltage VREF to be set to the same rating of short circuit trip level(Vsc=0.48V(Typ))
- Please select the external shunt resistance such that the SCP trip current is less than 1.7 times of the collector current rating I_c(DC).
- To prevent malfunction, the wiring of A, B, C should be as short as possible.
- OR output high level when protection works should be 0.505V(maximum V_{SC} rating) to 7V(CIN absolute maximum rating).

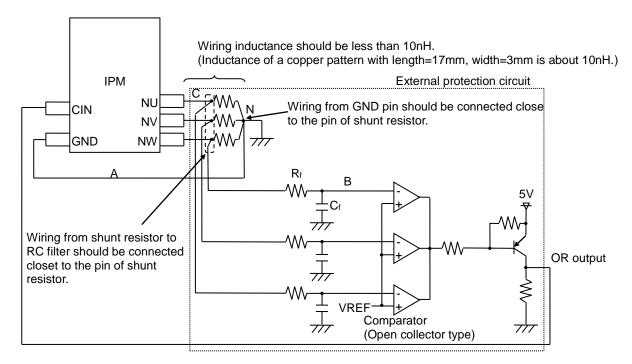


Figure 18. Wiring Pattern around the Shunt Resistor when operating with Three-shunt Resistors

I/O Equivalence Circuit

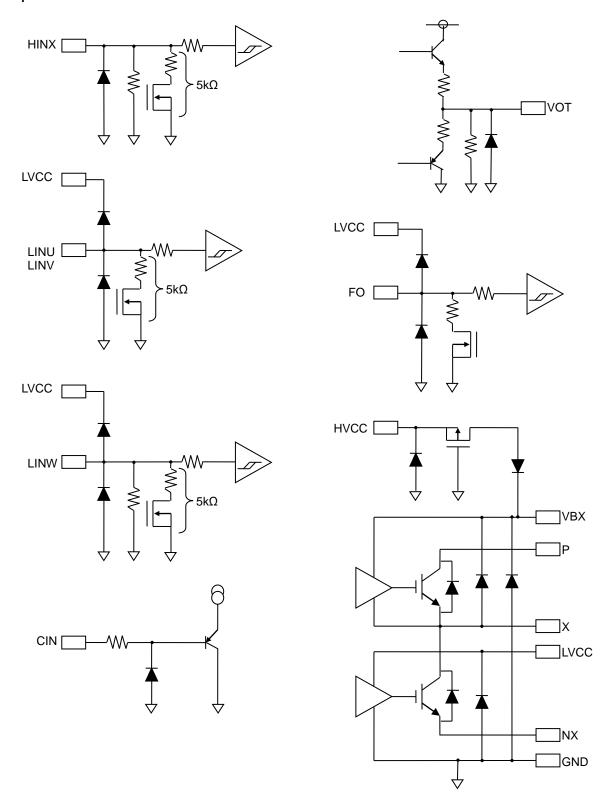


Figure 19. Input / Output Equivalent Circuit (X=U, V, W)

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IPM. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IPM's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition. However, pins that drive inductive loads (e.g. motor driver outputs, DC-DC converter outputs) may inevitably go below ground due to back EMF or electromotive force. In such cases, the user should make sure that such voltages going below ground will not cause the IPM and the system to malfunction by examining carefully all relevant factors and conditions such as motor characteristics, supply voltage, operating frequency and PCB wiring to name a few.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Thermal Consideration

Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip.

6. Recommended Operating Conditions

These conditions represent a range within which the expected characteristics of the IPM can be approximately obtained. The electrical characteristics are guaranteed under the conditions of each parameter.

7. Inrush Current

When power is first supplied to the IPM, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IPM has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

8. Testing on Application Boards

When testing the IPM on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IPM to stress. Always discharge capacitors completely after each process or step. The IPM's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IPM during assembly and use similar precautions during transport and storage.

9. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IPM on the PCB. Incorrect mounting may result in damaging the IPM. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

10. Unused Input Pins

Input pins of an IPM are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IPM. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

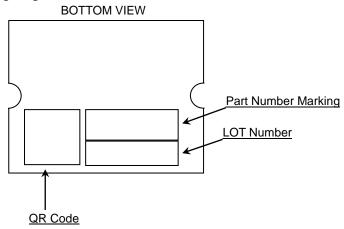
11. Area of Safe Operation (ASO)

Operate the IPM such that the output voltage, output current, and power dissipation are all within the Area of Safe Operation (ASO).

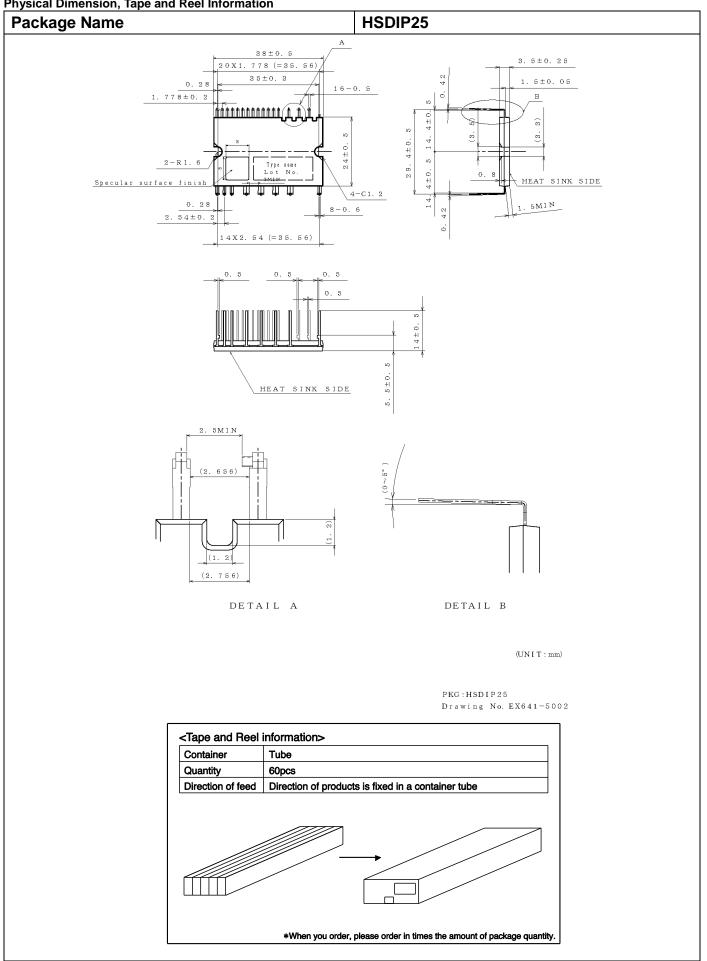
Ordering Information



Marking Diagram



Physical Dimension, Tape and Reel Information



Revision History

Date	Revision	Changes
04.Sep.2020	001	New Release

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 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
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- 8. Confirm that operation temperature is within the specified range described in the product specification.
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 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
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